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[International Rectifier \(Infineon Technologies Americas Corp.\)
IRGP4065DPBF](#)

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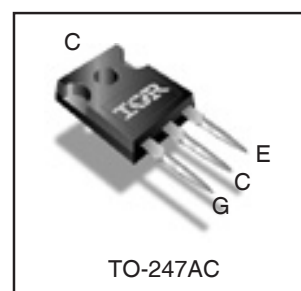
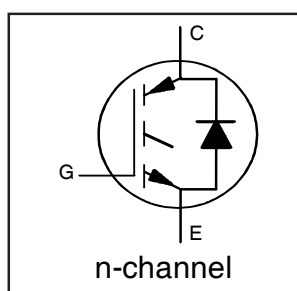
IRGP4065DPbF

PDP TRENCH IGBT

Features

- Advanced Trench IGBT Technology
- Optimized for Sustain and Energy Recovery Circuits in PDP Applications
- Low $V_{CE(on)}$ and Energy per Pulse (E_{PULSE}^{TM}) for Improved Panel Efficiency
- High Repetitive Peak Current Capability
- Lead Free Package

Key Parameters		
$V_{CE\ min}$	300	V
$V_{CE(ON)}\ typ.\ @\ I_C = 70A$	1.75	V
$I_{RP}\ max\ @\ T_C = 25^\circ C\ ①$	205	A
$T_J\ max$	150	$^\circ C$



G	C	E
Gate	Collector	Emitter

Description

This IGBT is specifically designed for applications in Plasma Display Panels. This device utilizes advanced trench IGBT technology to achieve low $V_{CE(on)}$ and low E_{PULSE}^{TM} rating per silicon area which improve panel efficiency. Additional features are 150 $^\circ C$ operating junction temperature and high repetitive peak current capability. These features combine to make this IGBT a highly efficient, robust and reliable device for PDP applications.

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{GE}	Gate-to-Emitter Voltage	± 30	V
$I_C\ @\ T_C = 25^\circ C$	Continuous Collector Current, $V_{GE}\ @\ 15V$	70	A
$I_C\ @\ T_C = 100^\circ C$	Continuous Collector, $V_{GE}\ @\ 15V$	40	
$I_{RP}\ @\ T_C = 25^\circ C$	Repetitive Peak Current ①	205	
$P_D\ @\ T_C = 25^\circ C$	Power Dissipation	160	W
$P_D\ @\ T_C = 100^\circ C$	Power Dissipation	63	
	Linear Derating Factor	1.3	W/ $^\circ C$
T_J	Operating Junction and	-40 to + 150	$^\circ C$
T_{STG}	Storage Temperature Range		
	Soldering Temperature for 10 seconds	300	
	Mounting Torque, 6-32 or M3 Screw	10lb·in (1.1N·m)	N

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$ (IGBT)	Thermal Resistance Junction-to-Case-(each IGBT) ②	—	0.80	$^\circ C/W$
$R_{\theta JC}$ (Diode)	Thermal Resistance Junction-to-Case-(each Diode) ②	1.45	2.5	
$R_{\theta CS}$	Case-to-Sink (flat, greased surface)	0.24	—	
$R_{\theta JA}$	Junction-to-Ambient (typical socket mount) ②	—	40	
	Weight	6.0 (0.21)	—	g (oz)

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 International


Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
BV_{CES}	Collector-to-Emitter Breakdown Voltage	300	—	—	V	$V_{GE} = 0V, I_{CE} = 1\text{mA}$
$\Delta BV_{CES}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.23	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_{CE} = 1\text{mA}$
$V_{CE(on)}$	Static Collector-to-Emitter Voltage	—	1.20	1.40	V	$V_{GE} = 15V, I_{CE} = 25A$ ③
		—	1.35	—		$V_{GE} = 15V, I_{CE} = 40A$ ③
		—	1.75	2.10		$V_{GE} = 15V, I_{CE} = 70A$ ③
		—	2.35	—		$V_{GE} = 15V, I_{CE} = 120A$ ③
		—	2.00	—		$V_{GE} = 15V, I_{CE} = 70A, T_J = 150^\circ\text{C}$
$V_{GE(th)}$	Gate Threshold Voltage	2.6	—	5.0	V	$V_{CE} = V_{GE}, I_{CE} = 500\mu\text{A}$
$\Delta V_{GE(th)}/\Delta T_J$	Gate Threshold Voltage Coefficient	—	-11	—	mV/ $^\circ\text{C}$	
I_{CES}	Collector-to-Emitter Leakage Current	—	2.0	25	μA	$V_{CE} = 300V, V_{GE} = 0V$
		—	50	—		$V_{CE} = 300V, V_{GE} = 0V, T_J = 150^\circ\text{C}$
I_{GES}	Gate-to-Emitter Forward Leakage	—	—	100	nA	$V_{GE} = 30V$
	Gate-to-Emitter Reverse Leakage	—	—	-100		$V_{GE} = -30V$
g_{fe}	Forward Transconductance	—	26	—	S	$V_{CE} = 25V, I_{CE} = 25A$
Q_g	Total Gate Charge	—	62	—	nC	$V_{CE} = 200V, I_C = 25A, V_{GE} = 15V$ ③
Q_{gc}	Gate-to-Collector Charge	—	20	—		
$t_{d(on)}$	Turn-On delay time	—	30	—		
t_r	Rise time	—	26	—	ns	$I_C = 25A, V_{CC} = 180V$ $R_G = 10\Omega, L = 200\mu\text{H}, L_S = 150\text{nH}$ $T_J = 25^\circ\text{C}$
$t_{d(off)}$	Turn-Off delay time	—	170	—		
t_f	Fall time	—	160	—		
$t_{d(on)}$	Turn-On delay time	—	30	—	ns	$I_C = 25A, V_{CC} = 180V$ $R_G = 10\Omega, L = 200\mu\text{H}, L_S = 150\text{nH}$ $T_J = 150^\circ\text{C}$
t_r	Rise time	—	28	—		
$t_{d(off)}$	Turn-Off delay time	—	250	—		
t_f	Fall time	—	310	—		
t_{st}	Shoot Through Blocking Time	100	—	—	ns	$V_{CC} = 240V, V_{GE} = 15V, R_G = 5.1\Omega$
E_{PULSE}	Energy per Pulse	—	875	—	μJ	$L = 220\text{nH}, C = 0.40\mu\text{F}, V_{GE} = 15V$ $V_{CC} = 240V, R_G = 5.1\Omega, T_J = 25^\circ\text{C}$
		—	975	—		$L = 220\text{nH}, C = 0.40\mu\text{F}, V_{GE} = 15V$ $V_{CC} = 240V, R_G = 5.1\Omega, T_J = 100^\circ\text{C}$
C_{iss}	Input Capacitance	—	2200	—	pF	$V_{GE} = 0V$ $V_{CE} = 30V$ $f = 1.0\text{MHz},$ See Fig.13
C_{oss}	Output Capacitance	—	110	—		
C_{rss}	Reverse Transfer Capacitance	—	55	—		
L_C	Internal Collector Inductance	—	5.0	—		
L_E	Internal Emitter Inductance	—	13	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact

Diode Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_{F(AV)}$	Average Forward Current at $T_C = 155^\circ\text{C}$	—	—	8.0	A	
I_{FSM}	Non Repetitive Peak Surge Current	—	—	100	A	$T_J = 155^\circ\text{C}, PW = 6.0\text{ms}$ half sine wave
V_F	Forward Voltage	—	1.0	1.25	V	$I_F = 8A$
		—	0.83	1.0		$I_F = 8A, T_J = 125^\circ\text{C}$
t_{rr}	Reverse Recovery Time	—	—	35	ns	$I_F = 1A, di/dt = -50A/\mu\text{s}, V_R = 30V$
		—	27	—		$T_J = 25^\circ\text{C}$
		—	40	—		$T_J = 125^\circ\text{C}$
Q_{rr}	Reverse Recovery Charge	—	30	—	nC	$I_F = 8A$ $di/dt = 200A/\mu\text{s}$ $V_R = 200V$
		—	106	—		
I_{rr}	Peak Recovery Current	—	2.2	—	A	$T_J = 25^\circ\text{C}$
		—	5.3	—		$T_J = 125^\circ\text{C}$

Notes:

- ① Half sine wave with duty cycle = 0.25, $t_{on} = 1\mu\text{sec}$.
 ② R_G is measured at T_J of approximately 90°C .

③ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.

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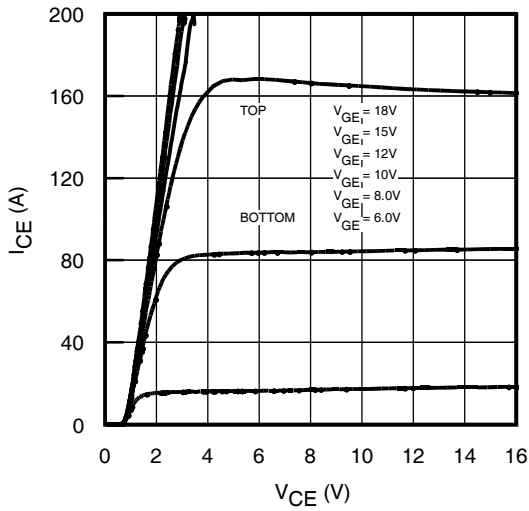


Fig 1. Typical Output Characteristics @ 25°C

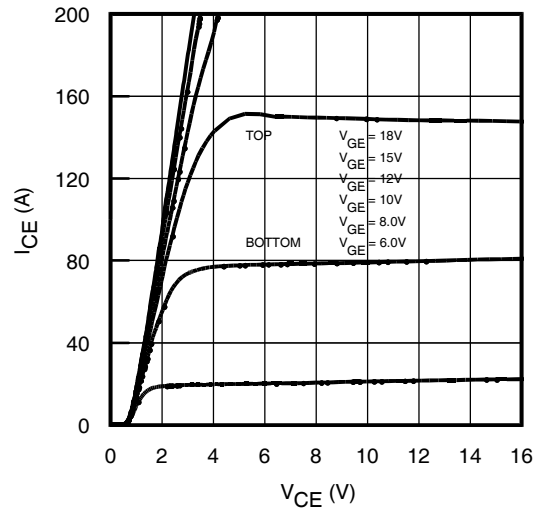


Fig 2. Typical Output Characteristics @ 75°C

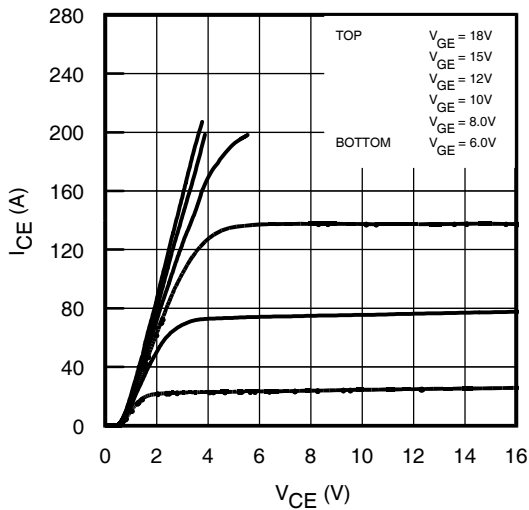


Fig 3. Typical Output Characteristics @ 125°C

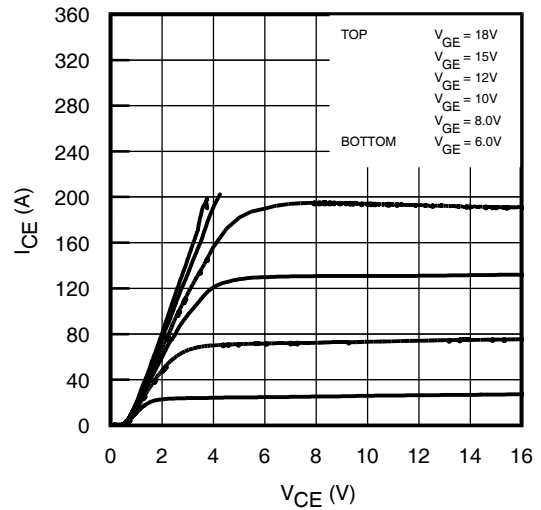


Fig 4. Typical Output Characteristics @ 150°C

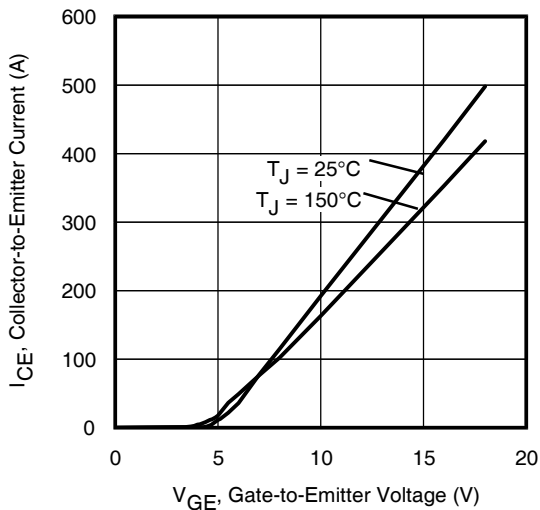


Fig 5. Typical Transfer Characteristics

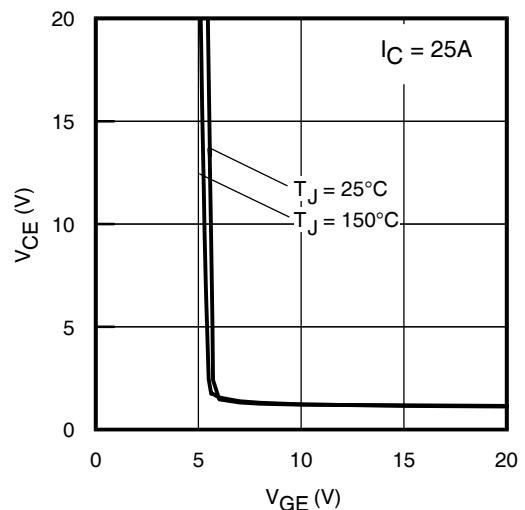


Fig 6. $V_{CE(ON)}$ vs. Gate Voltage

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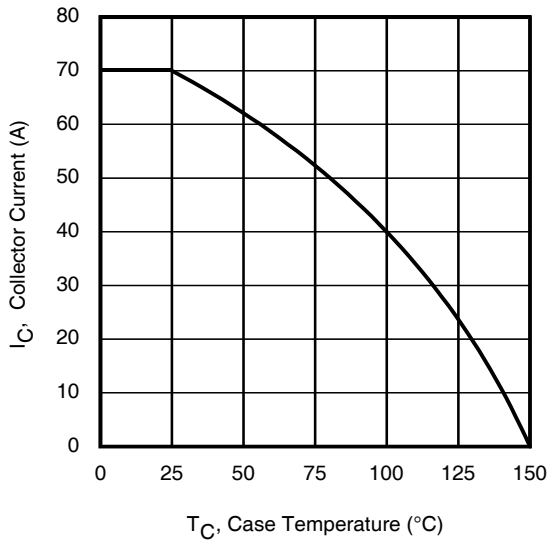


Fig 7. Maximum Collector Current vs. Case Temperature

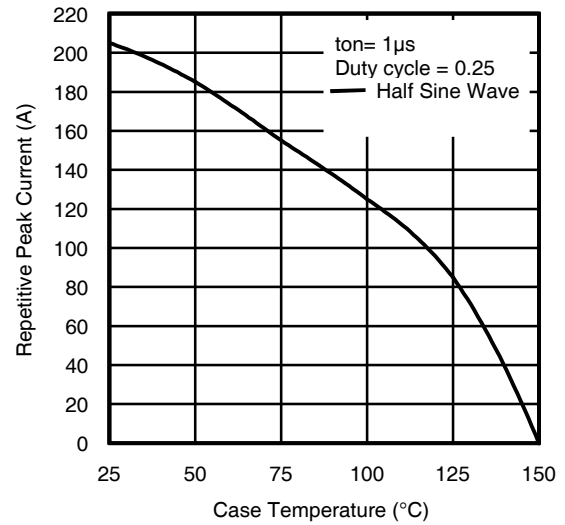


Fig 8. Typical Repetitive Peak Current vs. Case Temperature

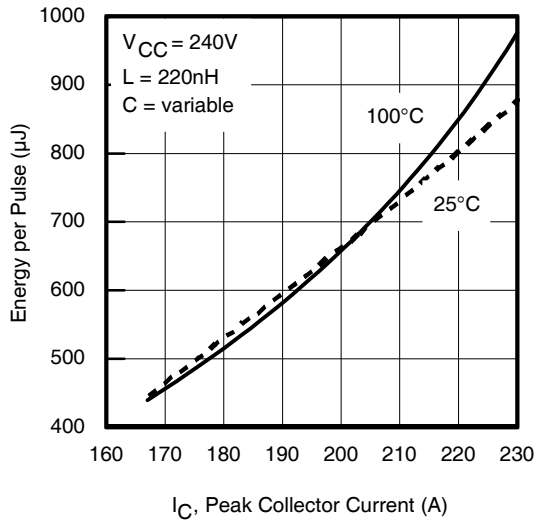


Fig 9. Typical E_{PULSE} vs. Collector Current

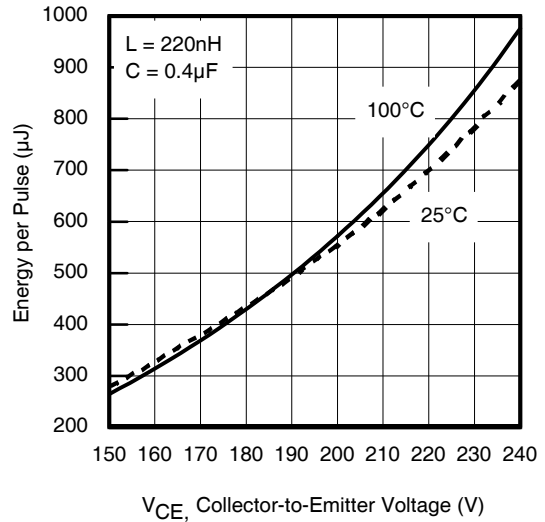


Fig 10. Typical E_{PULSE} vs. Collector-to-Emitter Voltage

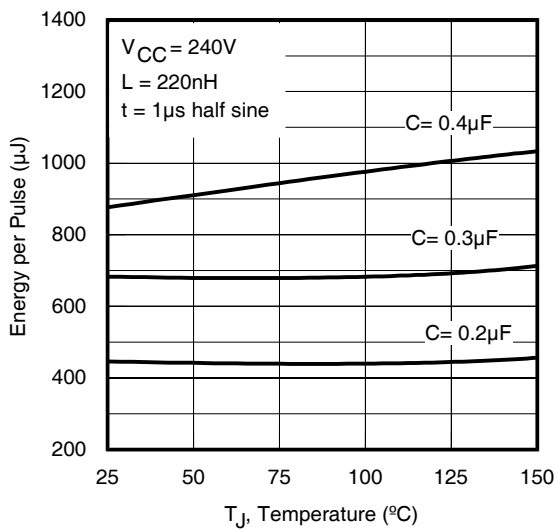


Fig 11. E_{PULSE} vs. Temperature

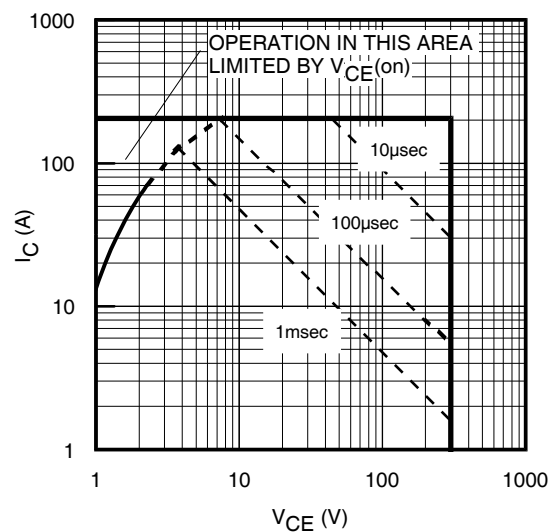


Fig 12. Forward Bias Safe Operating Area

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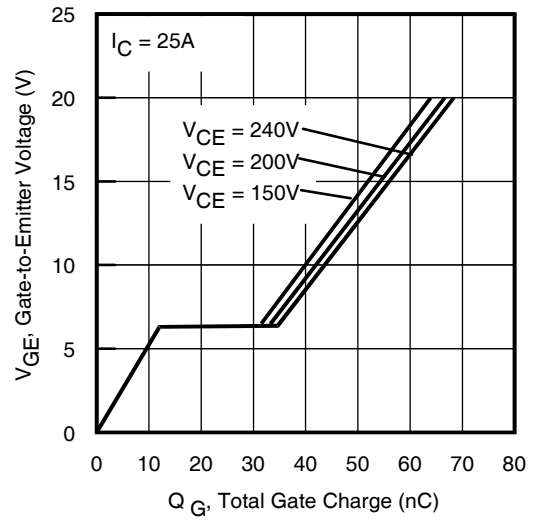
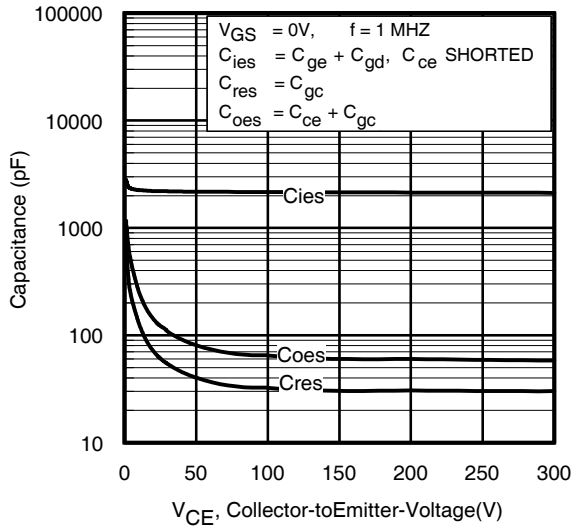


Fig 13. Typical Capacitance vs. Collector-to-Emitter Voltage

Fig 14. Typical Gate Charge vs. Gate-to-Emitter Voltage

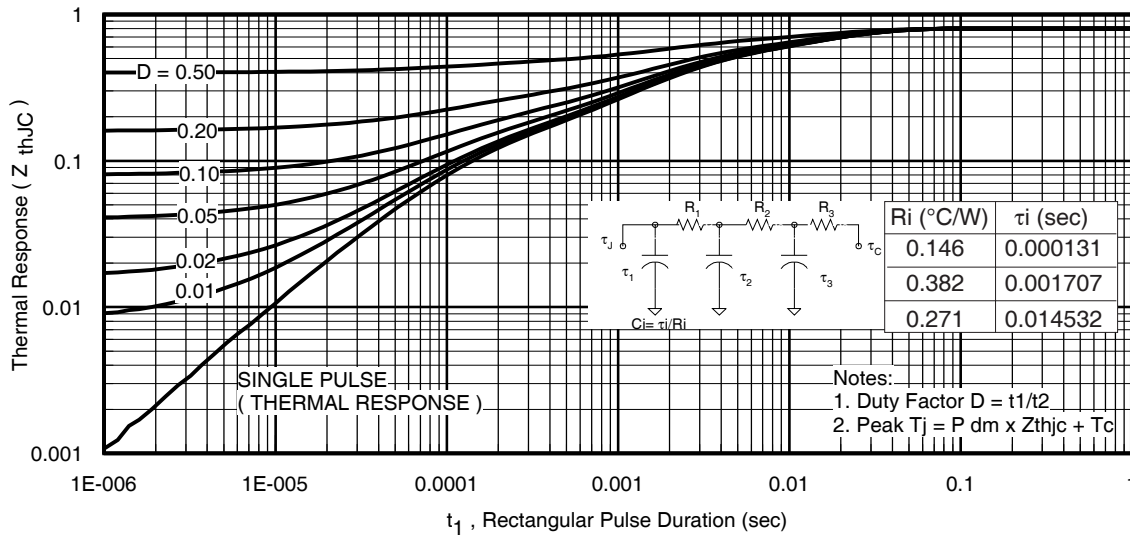


Fig 15. Maximum Effective Transient Thermal Impedance, Junction-to-Case (IGBT)

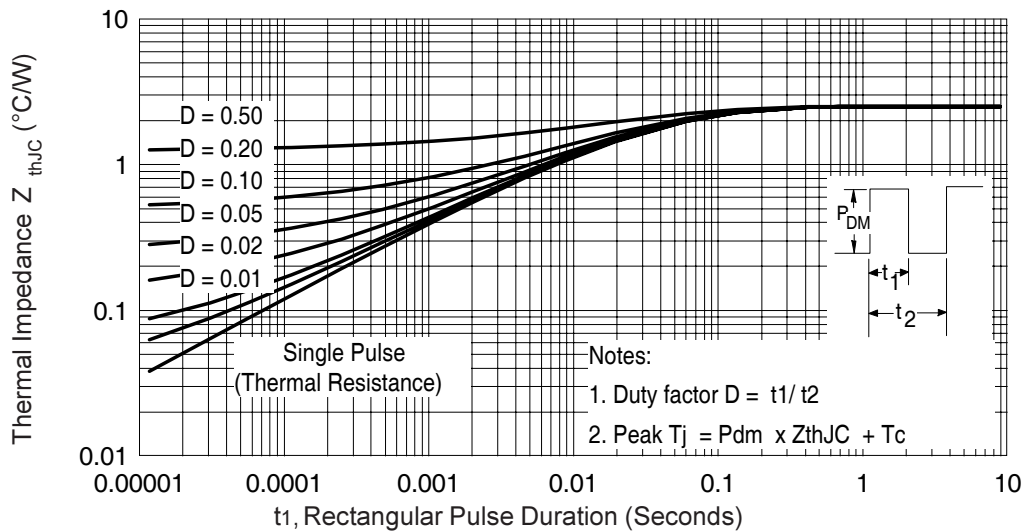


Fig 16. Maximum Effective Transient Thermal Impedance, Junction-to-Case (DIODE)

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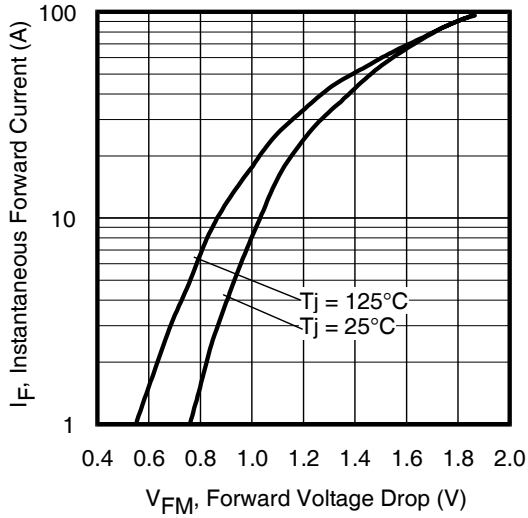


Fig. 17 - Typical Forward Voltage Drop Characteristics

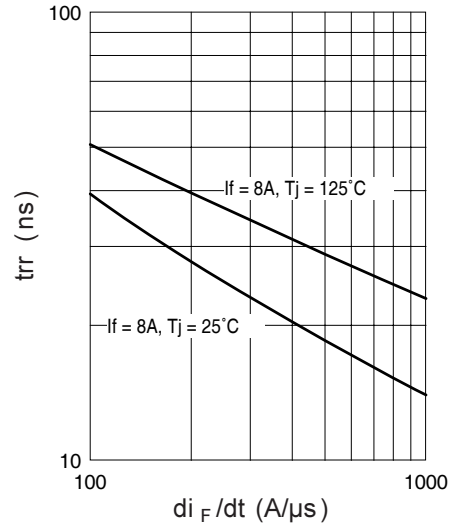


Fig. 18 - Typical Reverse Recovery vs. di_F/dt

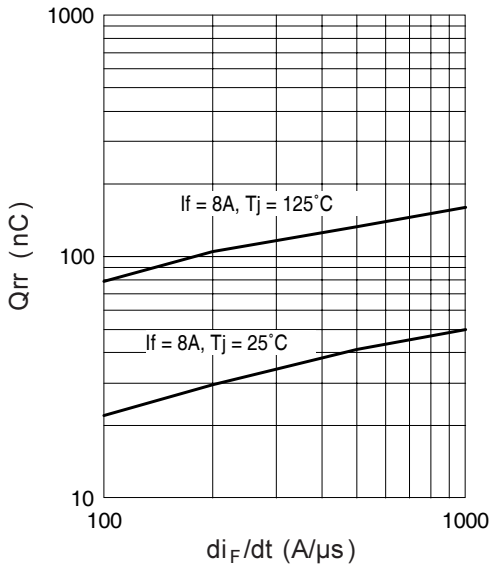


Fig. 19 - Typical Stored Charge vs. di_F/dt

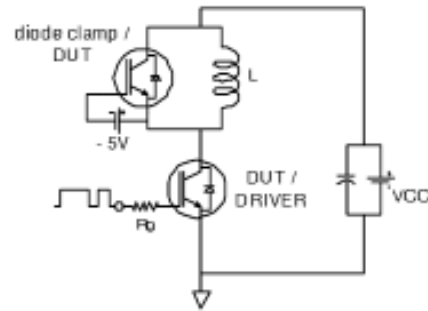


Fig. 20 - Switching Loss Circuit

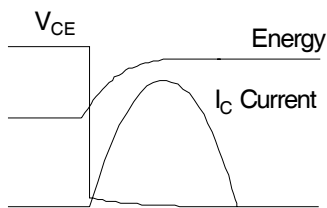


Fig 21b. t_{st} Test Waveforms

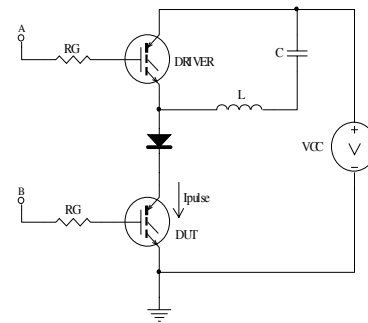


Fig 21a. t_{st} and E_{PULSE} Test Circuit

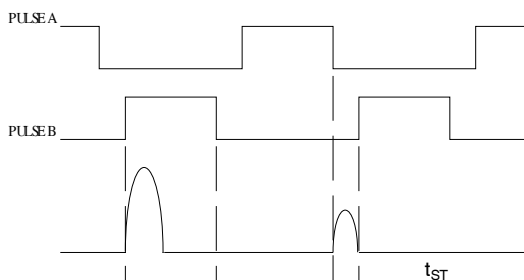


Fig 21c. E_{PULSE} Test Waveforms

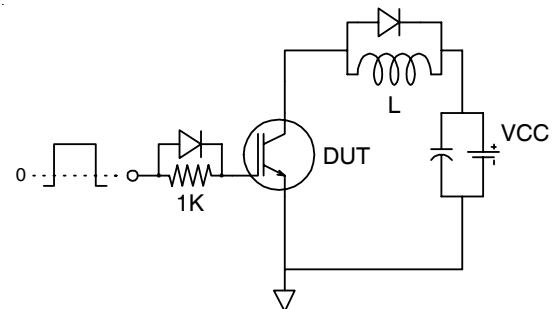
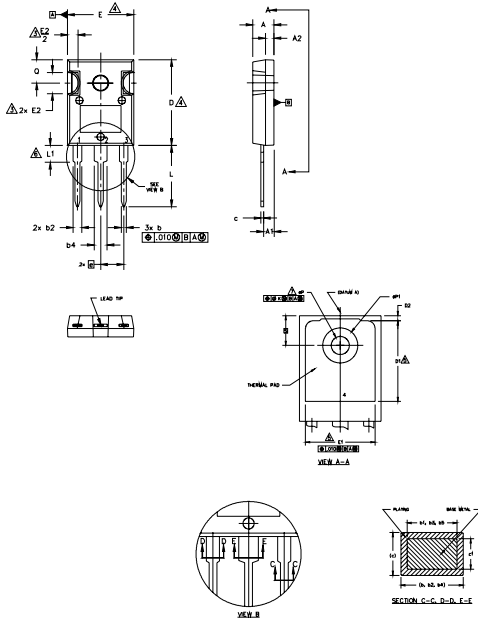


Fig. 22 - Gate Charge Circuit (turn-off)

TO-247AC Package Outline Dimensions are shown in millimeters (inches)



- NOTES:
1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M 1994.
 2. DIMENSIONS ARE SHOWN IN INCHES.
 3. CONTOUR OF SLOT OPTIONAL.
 4. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
 5. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS D1 & E1.
 6. LEAD FINISH UNCONTROLLED IN L1.
 7. #P TO HAVE A MAXIMUM DRAFT ANGLE OF 1.5 ° TO THE TOP OF THE PART WITH A MAXIMUM HOLE DIAMETER OF .154 INCH.
 8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-247AC.

SYMBOL	INCHES		MILLIMETERS		NOTES
	MIN.	MAX.	MIN.	MAX.	
A	.183	.209	4.65	5.31	
A1	.087	.102	2.21	2.59	
A2	.059	.098	1.50	2.49	
b	.039	.055	0.99	1.40	
b1	.039	.053	0.99	1.35	
b2	.065	.094	1.65	2.39	
b3	.065	.092	1.65	2.34	
b4	.102	.135	2.59	3.43	
b5	.102	.133	2.59	3.38	
c	.015	.035	0.38	0.89	
c1	.015	.033	0.38	0.84	
D	.776	.815	19.71	20.70	4
D1	.515	-	13.08	-	5
D2	.020	.053	0.51	1.35	
E	.602	.625	15.29	15.87	4
E1	.530	-	13.46	-	
E2	.178	.216	4.52	5.49	
e	.215 BSC	-	5.46 BSC	-	
e1	.010	-	0.25	-	
L	.559	.634	14.20	16.10	
L1	.146	.169	3.71	4.29	
#P	.140	.144	3.56	3.66	
#P1	-	.291	-	7.39	
Q	.209	.224	5.31	5.69	
S	.217 BSC	-	5.51 BSC	-	

LEAD ASSIGNMENTS

- HEXFEET
 1- GATE
 2- DRAIN
 3- SOURCE
 4- DRAIN

IGBTs, CoPACK

- 1- GATE
 2- COLLECTOR
 3- EMITTER
 4- COLLECTOR

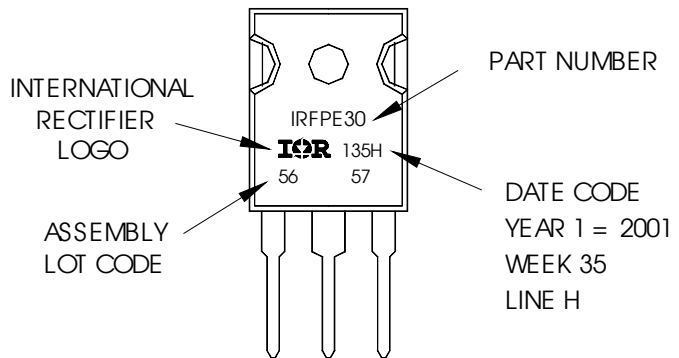
DIODES

- 1- ANODE/OPEN
 2- CATHODE
 3- ANODE

TO-247AC Part Marking Information

EXAMPLE: THIS IS AN IRFPE30
 WITH ASSEMBLY
 LOT CODE 5657
 ASSEMBLED ON WW 35, 2001
 IN THE ASSEMBLY LINE "H"

Note: "P" in assembly line position indicates "Lead-Free"



TO-247AC package is not recommended for Surface Mount Application.

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Data and specifications subject to change without notice. This product has been designed for the Industrial market. Qualification Standards can be found on IR's Web site.

Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>